Search Notes

L	Hits	Search Text	DB	Time stamp
Number				
-	3	("6613653").PN.	USPAT; US-PGPUB;	2004/05/31 19:18
-	3	("6339013").PN.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/31 19:20
-	482	(438/682).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/31 19:59
-	626	(438/683).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/31 19:59
-	514	(438/597).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/31 20:00
-	7696	polysilicon and amorphous and anneal\$3	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/31 20:00
-	4111	polysilicon and amorphous same anneal\$3	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/05/31 20:00
_	3259	polysilicon and amorphous with silicon same anneal\$3	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/31 20:01
_	828	polysilicon and amorphous with silicon same anneal\$3 and ("200" or "300" or "400" or "500") with temperature	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/31 20:02
-	208	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/31 20:03
-	171	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and metal	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/05/31 20:04
_	113	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and aluminum	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:20
_	5	polysilicon and amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500") with temperature same aluminum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/05/31 21:06
-	1		USPĀT	2004/05/31 21:04

-	256	"5275851"	USPAT; US-PGPUB;	2004/05/31 21:07
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	226	"5275851" and aluminum and amorphous adj	USPAT; US-PGPUB;	2004/05/31 21:09
			EPO; JPO;	
	· '		DERWENT; IBM TDB	
-	55	·	USPĀT; US-PGPUB;	2004/05/31
		adj silicon	EPO; JPO;	21:09
			DERWENT; IBM TDB	
-	23	· ·	USPAT;	2004/05/31
		adj silicon same anneal\$3	US-PGPUB; EPO; JPO;	21:20
			DERWENT;	
-	16		IBM_TDB USPAT;	2004/05/31
		same anneal\$3 same ("200" or "300" or "400" or "500") with temperature and	US-PGPUB; EPO; JPO;	21:23
		aluminum same crystallization	DERWENT;	
_	11	polysilicon and amorphous with silicon	IBM_TDB USPAT;	2004/05/31
		same anneal\$3 same ("200" or "300" or	US-PGPUB;	23:56
		"400" or "500") with temperature same metal same crystallization	EPO; JPO; DERWENT;	
_	21	polysilicon and amorphous with silicon	IBM_TDB USPAT;	2004/06/01
		same anneal\$3 same ("200" or "300" or	US-PGPUB;	00:08
		"400" or "500") with temperature and mic	EPO; JPO; DERWENT;	
	26	amanuhana wikh siliaan sama anna 102	IBM_TDB	2004/06/01
	20	amorphous with silicon same anneal\$3 same ("200" or "300" or "400" or "500")	USPAT; US-PGPUB;	2004/06/01 00:08
		with temperature and mic	EPO; JPO; DERWENT;	
		140	IBM_TDB	0004/05/01
_	8	amorphous with silicon same anneal\$3 with temperature and mic same al	USPAT; US-PGPUB;	2004/06/01
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	57	amorphous with silicon same anneal\$3 with temperature and mic	USPAT; US-PGPUB;	2004/06/01
		-	EPO; JPO;	
			DERWENT; IBM_TDB	
-	87	amorphous with silicon same anneal\$3	USPAT; US-PGPUB;	2004/06/01
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	625	amorphous with silicon same anneal\$3 and metal with crystallization	USPAT; US-PGPUB;	2004/06/01
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	77	amorphous with silicon same anneal\$3 and metal near crystallization	USPAT; US-PGPUB;	2004/06/01 00:15
		and model near orystatilization	EPO; JPO;	00.13
			DERWENT; IBM TDB	
-	87	amorphous with silicon same anneal\$3	USPAT;	2004/06/01
		and mrc	US-PGPUB; EPO; JPO;	02.40
		·	DERWENT; IBM TDB	

1	432	(438/486).CCLS.	USPAT;	2004/06/01
			US-PGPUB;	02:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	729	(438/482).CCLS.	USPAT;	2004/06/01
		·	US-PGPUB;	02:40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	